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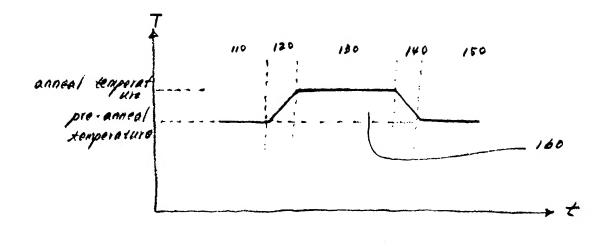


Fig. 1



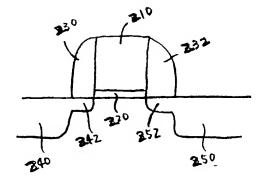


Figure 2

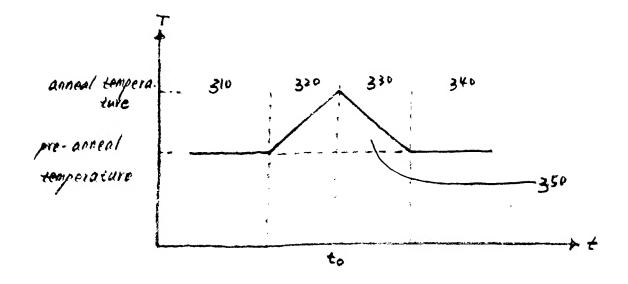
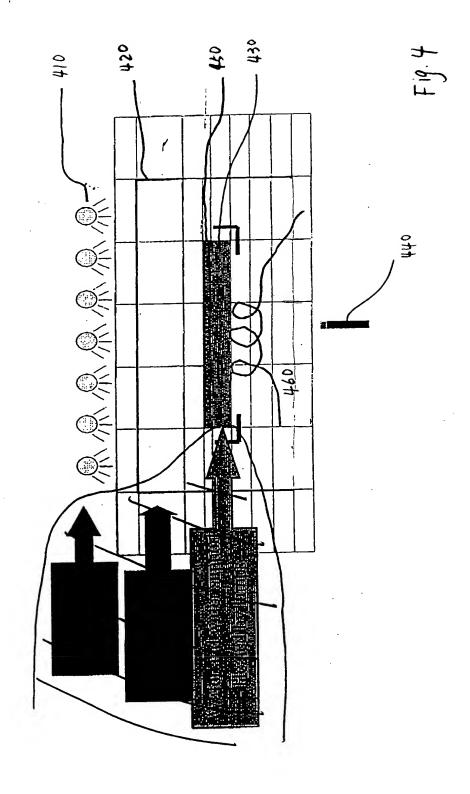


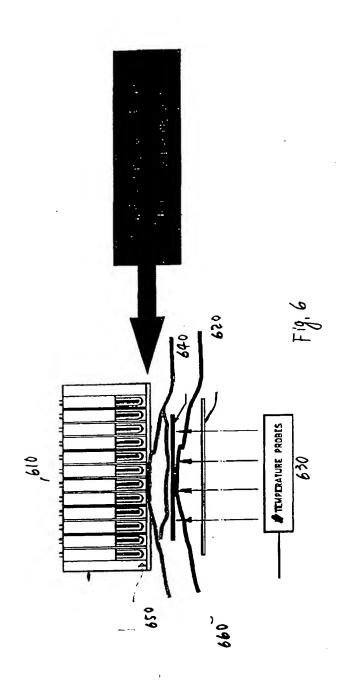
Fig 3

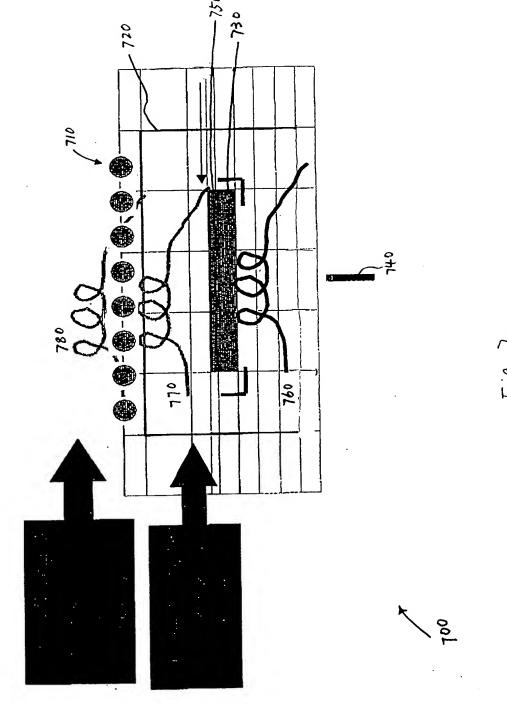
RTP Chamber brief structure





Spike annealing process temperature profile 1100.00 650,00 600,00 700,00 T50.00 1050, 00 1000.00 950.00 900,00 850,00 800,00





Mattson RTP system

1. of

Turning On At Least 810

One Heat Source Heating a Semiconductor 820 Substrate in a Chamber Turning Off at Least One N830
Heal Source Cooling the Semiconductor 640
Substrate With Gas Flow

Figure 8